Toshiba Bipolar Linear Integrated Circuit Silicon Monolithic

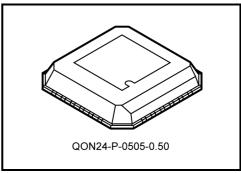
# **TA8496FL**

### Magnetic Head R/W IC

This IC enables writing and detection of magnetic recording signals.

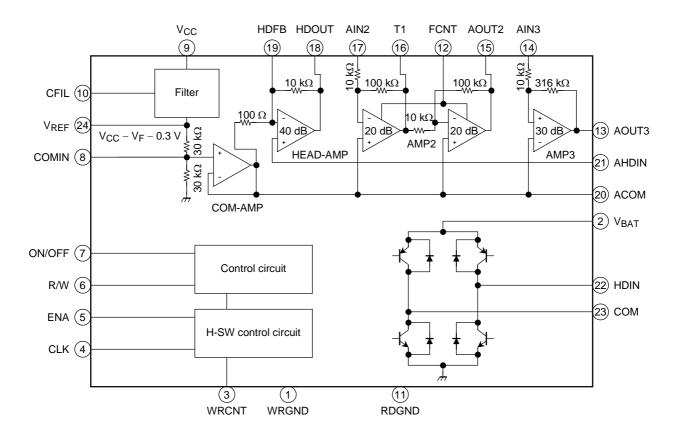
#### **Features**

- Operating voltage range:  $V_{CC} = 3.5$  to 7 V  $V_{BAT} = 1.8$  to 7 V
- Output current:  $I_{out} = 20 \text{ mA (max)}$
- Constant current operating function
  - $: I_{OC} = (0.25 \text{ (V)} \times 160 \text{ (A)}) / R_{WR} \text{ (typ.)}$



Weight: 0.05 g (typ.)

### **Block Diagram**



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## **Pin Function**

Pin Number	Symbol	Description
1	WRGND	GND for write block
2	V <sub>BAT</sub>	High-switch control power supply
3	WRCNT	Write output setting pin
4	CLK	High-switch operation control signal input
5	ENA	High-switch enable signal input
6	R/W	Read/write select signal input
7	ON/OFF	Chip enable signal input
8	COMIN	Internal reference voltage setting (fine adjustment)
9	Vcc	Power supply input pin
10	CFIL	Power supply filter connecting pin (C = 0.1 $\mu$ F)
11	RDGND	GND for read block
12	FCNT	Cut-off frequency setting pin
13	AOUT3	Amp 3 output
14	AIN3	Amp 3 input
15	AOUT2	Amp 2 output
16	T1	Amp 2 test pin
17	AIN2	Amp 2 input
18	HDOUT	Head amp output
19	HDFB	Head amp feedback input
20	ACOM	COM amp output
21	AHDIN	Head amp output
22	HDIN	Write output
23	СОМ	Write output
24	V <sub>ref</sub>	V <sub>CC</sub> filter output (internal power supply)

# Maximum Rating (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Power Supply Voltage	V <sub>CC</sub>	8	V
Power Supply Voltage	V <sub>BAT</sub>	8	V
Input Voltage	VI	6	V
Output Current	lout	20	mA
Operating Temperature	T <sub>opr</sub>	-20 to 70	°C
Storage Temperature	T <sub>stg</sub>	-50 to 150	°C

# **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit
Power Supply Voltage	V <sub>CC</sub>	3.5 to 7.0	V
Tower Supply Voltage	V <sub>BAT</sub>	1.8 to 7.0	V

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### **Functions**

	Inp	out	Write	Read Unit		
ON/OFF	R/W	ENA	CLK	COM	HDin	itead Offit
	Н	H/L	H/L	× ×	$\infty$	Enable
	L	Н	Н	L	Н	Disable
Н	L	Н	L	Н	L	Disable
	L	L	L	L	L	Disable
	L	L	Н	∞	∞	Disable
L	H/L	H/L	H/L	× ×	8	Disable

 $<sup>\</sup>infty \hbox{: High impedance}$ 

### **Electrical Characteristics**

## Interface Block (unless otherwise is specified, $V_{CC} = 5 \text{ V}$ , $V_{BAT} = 3 \text{ V}$ , $Ta = 25 ^{\circ}\text{C}$ )

Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
	V <sub>IN1-Hi</sub>	_	ENA, ON/OFF	2.5	_	$V_{CC}$	
Input Voltage	V <sub>IN1-Lo</sub>	_	ENA, ON/OFF	_	_	1.0	V
input voltage	V <sub>IN2-Hi</sub>	_	CLK, R/W	1.5	_	V <sub>C</sub> C	
	V <sub>IN2-Lo</sub>	_	CLK, R/W	_	_	0.5	
	I <sub>IN1-Hi</sub>		CLK, V <sub>IN</sub> = 5 V		15	25	
	I <sub>IN1-Lo</sub>		CLK, V <sub>IN</sub> = 0 V		-85	-120	
Innut Current	I <sub>IN2-Hi</sub>		ENA, V <sub>IN</sub> = 5 V		85	120	
Input Current	I <sub>IN3-Hi</sub>	1	R/W, V <sub>IN</sub> = 5 V	_	15	25	μΑ
	I <sub>IN3-Lo</sub>	N3-Lo	R/W, V <sub>IN</sub> = 0 V	_	-85	-120	
	I <sub>IN4-Hi</sub>		ON/OFF, V <sub>IN</sub> = 5 V	_	85	120	



## Read Block (unless otherwise is specified, $V_{CC} = 5 \text{ V}$ , $V_{BAT} = 3 \text{ V}$ , $Ta = 25^{\circ}\text{C}$ )

Chara	acteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
	Current Dissipation			When read block in operation	_	3.2	4.6	mA
Current Dissipation			2	When chip disabled	_	0	1	μА
		Icco		(on/off = low or open)				•
	Head amp	G <sub>H</sub>		_		40	_	
Gain Characteristics	Amp 2	G <sub>2</sub>	3	_	_	40	_	dB
	Amp 3	G <sub>3</sub>		_	_	30	_	
Hood Amp Input	Head Amp Input Conversion Noise			$R_g = 0 \Omega$ , $f_c = 19 \text{ kHz}$	_	0.33	(0.64)*	\/
nead Amp input (			Ī —	$R_g = 0 \Omega$ , $f_c = 1.7 \text{ kHz}$	_	0.15	(0.26)*	μV <sub>rms</sub>
Reference Voltag	е	V <sub>ACOM</sub>	3	_	1.9	2.0	2.1	V
	Head amp V <sub>HOS</sub>			_	-0.1	±0.25		
Output Offset Voltage	Amp 2	V <sub>2OS</sub>	3	_	_	+0.7	±1.1	V
	Amp 3	V <sub>3OS</sub>			_	+0.1	±0.25	
Amp 3 Output	Low	V <sub>3OL</sub>	4	P 10 kO	_	0.2	_	V
Voltage Range	High	V <sub>3OH</sub>	7 *	$R_L = 10 \text{ k}\Omega$	_	4.1	_	V
Amp 3 Output	Output	I <sub>3OUT</sub>	4	_	2.0	_	_	mA
Current	Input	I <sub>3IN</sub>	7 *	_	0.1	0.2	0.3	IIIA

<sup>\*:</sup> Guaranteed by design. Determined at design and does not change at manufacturing. Test not conducted.

### Write Block (unless otherwise is specified, $V_{CC} = 5 \text{ V}$ , $V_{BAT} = 3 \text{ V}$ , $Ta = 25^{\circ}\text{C}$ )

Characteristics	Symbol	Test Circuit	Test Condition		Min	Тур.	Max	Unit
	I <sub>CCw</sub>		During write, CLK = Low/High		_	3.7	5.2	
	I <sub>CCe</sub>		When write enabled		_	1.9	2.8	
	I <sub>CCB</sub>		When write in break		_	4.4	6.1	mA
Current Dissipation	I <sub>bat</sub>	2	During write, reactive current $(R_{WR} = 5 \; k\Omega)$		_	1.4	1.8	IIIA
	I <sub>baB</sub>		When write in break		_	1.0	1.6	
	I <sub>bar</sub>		During read		_	0	1	
	I <sub>bao</sub>		When chip disabled (on/off = low or open)		_	0	1	μΑ
Sat Output Current	loc	5	I <sub>OC</sub> = 10 mA	V <sub>BAT</sub> = 2.0 V	8	10	12	- mA
Set Output Current			(at V <sub>BAT</sub> = 2.0 V)	V <sub>BAT</sub> = 5.0 V	_	11	13	
	T <sub>pLH1</sub>		0 to 10%	0% (Note1)		0.1	_	
CLK Output Transfer Time	T <sub>pLH2</sub>	6	0 to 90% (Note1)		_	0.5	_	0
CLR Output Transfer Time	T <sub>pHL1</sub>	0	0 to 10% (Note1)		_	0.1	_	μS
	T <sub>pHL2</sub>		0 to 90% (Note1)		_	0.5	_	
	T <sub>pZH1</sub>		0 to 10% (Note1)		_	0.3	_	
ENA Output Transfer Time	T <sub>pZH2</sub>	6	0 to 90% (Note1)		_	0.5		
LIVA Output Transier Time	T <sub>pHZ1</sub>		0 to 10% (Note1)		_	0.3	_	μS
	T <sub>pHZ2</sub>		0 to 90% (Note1)		_	0.5	_	

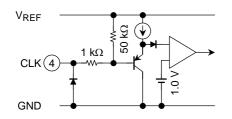
Note 1: Load RL = 36  $\Omega$ , CL = 10 pF

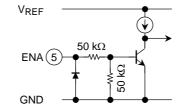
## **Input/Output Circuit**

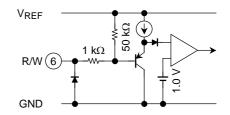
• CLK pin



• R/W pin

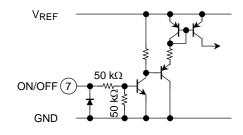


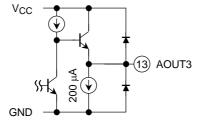




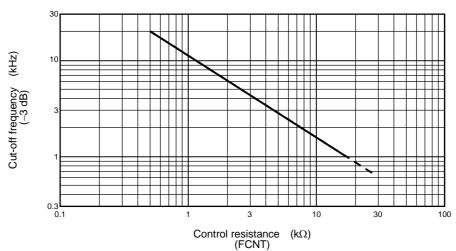
• ON/OFF pin

• AOUT3 pin





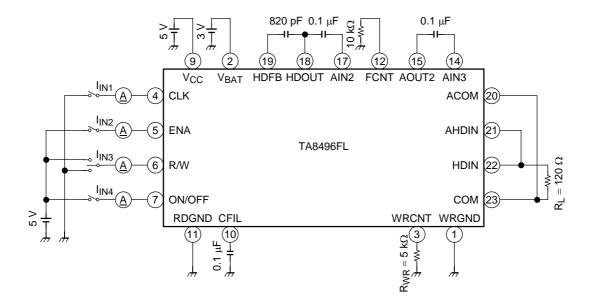
Secondly L.P.F characteristics (amp 2)



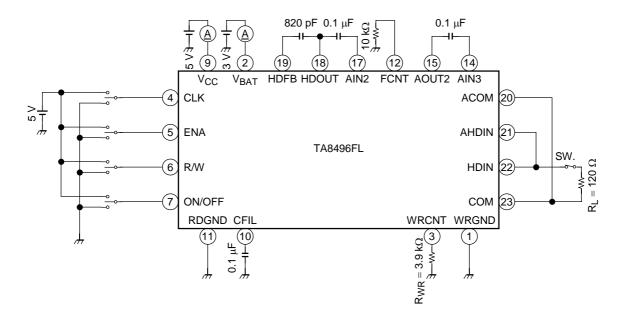
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### **Test Circuit**

# 1. Input Current (I<sub>IN1</sub>, I<sub>IN2</sub>, I<sub>IN3</sub>, I<sub>IN4</sub>)



## 2. Current Consumption (I<sub>CCR</sub>, I<sub>CCO</sub>, I<sub>CCW</sub>, I<sub>CCe</sub>, I<sub>CCB</sub>, I<sub>bat</sub>, I<sub>baB</sub>, I<sub>bar</sub>, I<sub>bao</sub>)

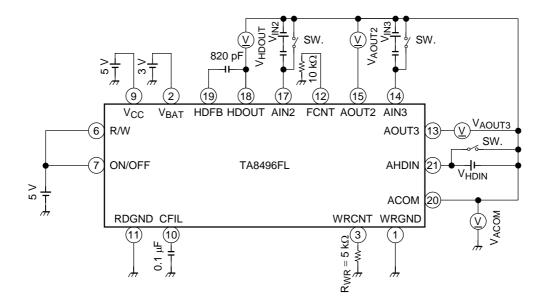


Input Sequence (H = 5 V, L = 0 V)

Current Consumption (V <sub>CC</sub> , V <sub>BAT</sub> )	ON/OFF	R/W	ENA	CLK
I <sub>CCR</sub>	Н	Н	L	Н
Icco	L/OPEN	Н	H/L	Н
I <sub>CCW</sub>	Н	L	Н	H/L
I <sub>CCe</sub>	Н	L	L	Н
I <sub>CCB</sub>	Н	L	L	L
I <sub>bat</sub> (Note2)	Н	L	Н	H/L
I <sub>baB</sub>	Н	L	L	L
I <sub>bar</sub>	Н	Н	H/L	H/L
I <sub>bao</sub>	L/OPEN	H/L	H/L	H/L

Note 2: SW. OFF

### 3. Gain Characteristics (G<sub>H</sub>, G<sub>2</sub>, G<sub>3</sub>), Power Off-Set Voltage (V<sub>HOS</sub>, V<sub>2OS</sub>, V<sub>3OS</sub>)

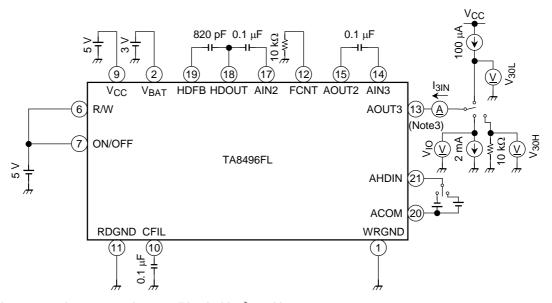


$$G_{H} = 20 \log \left| \frac{V_{HDOUT}}{V_{HDIN}} \right|, G_{2} = 20 \log \left| \frac{V_{AOUT2}}{V_{IN2}} \right|, G_{3} = 20 \log \left| \frac{V_{AOUT3}}{V_{IN3}} \right|$$

When off-set voltage is measured, SW turns ON.

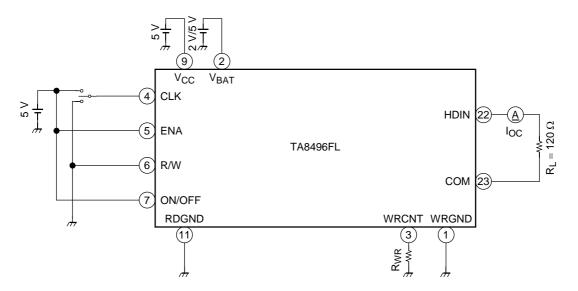
 $V_{HOS} = |V_{HDOUT}|, V_{2OS} = |V_{AOUT2}|, V_{3OS} = |V_{AOUT3}|$ 

### 4. Amp 3 Output Voltage Range (V<sub>3OL</sub>, V<sub>3OH</sub>), Amp 3 Output Current (I<sub>3OUT</sub>, I<sub>3IN</sub>)



Note 3:  $I_{3OUT}$  must be measured on condition in  $V_{IO} \ge 4.0 \text{ V}$ 

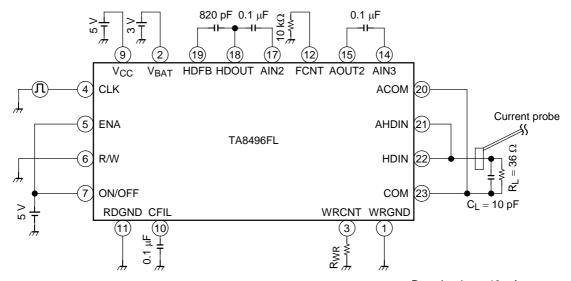
### 5. Set Output Current (I<sub>OC</sub>)



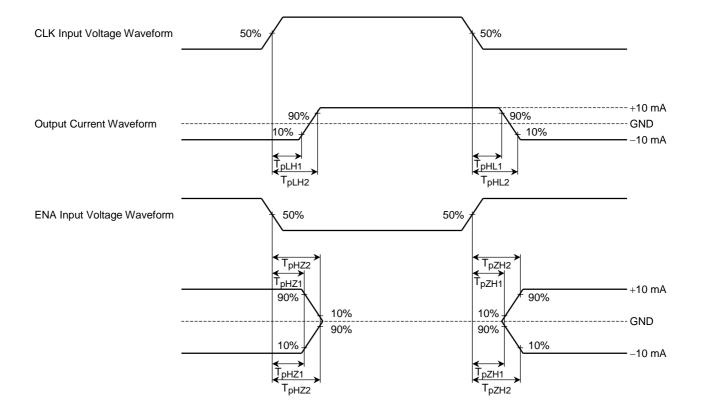
Set RWR so that IOC = 10 mA (at VBAT = 2 V).

At this time, due to fluctuation in samples,  $I_{OC}$  fluctuates in the range of 8 to 12 mA. Also,  $I_{OC}$  fluctuates depending on the power supply (V<sub>BAT</sub>) as follows:  $I_{OC}$  = 10 mA (at V<sub>BAT</sub> = 2 V)  $\rightarrow$   $I_{OC}$   $\simeq$  13 mA (at V<sub>BAT</sub> = 5 V).

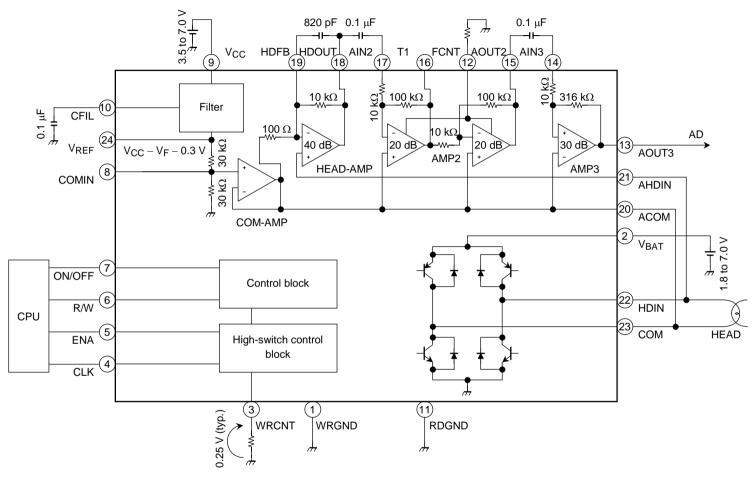
# 6. CLK, ENA Output Propagation Time (T<sub>pLH1/2</sub>, T<sub>pHL1/2</sub>, T<sub>pZH1/2</sub>, T<sub>pHZ1/2</sub>)



 $R_{WR}\!:$   $I_{OC}$  is set 10 mA.



### **Example of Application Circuit**



Note 4: Operating supply voltage range

 $V_{CC} = 3.5$  to 7.0 V,  $V_{BAT} = 1.8$  to 7.0 V

However, set V<sub>CC</sub> so that  $V_{ACOM} \le V_{BAT} + 0.5 \text{ V}$ .  $V_{CC} \ge V_{BAT}$ .

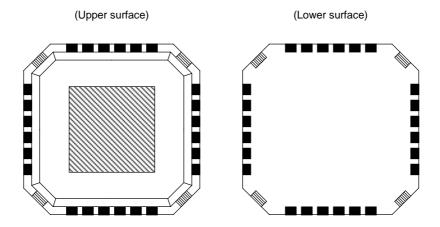
 $(V_{ACOM} = (V_{CC} - VF - 0.3)/2)$ 

By connecting a resistor to the COMIN pin, VACOM can be varied.

Note 5: The IC may be damaged by shorts between pins, to the power supply, or to ground. Take great care when designing lines.

#### **Requests Concerning Use of QON**

#### **Outline Drawing of Package**



When using QON, please take into account the following items.

#### Caution

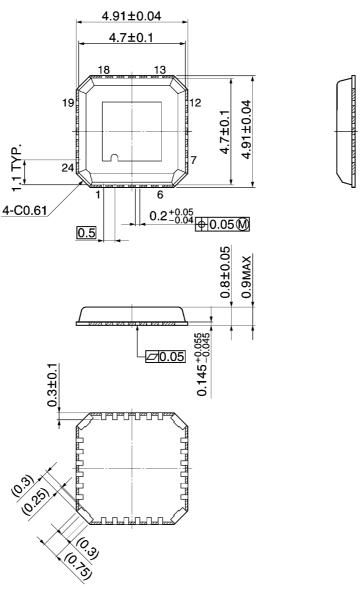
- (1) Do not carry out soldering on the island section in the four corners of the package (the section shown on the lower surface drawing with diagonal lines) with the aim of increasing mechanical strength.
- (2) The island section exposed on the package surface (the section shown on the upper surface drawing with diagonal lines) must be used as (Note 6) below while electrically insulated from outside.

Note 6: Ensure that the island section (the section shown on the lower surface drawing with diagonal lines) does not come into contact with solder from through-holes on the board layout.

- When mounting or soldering, take care to ensure that neither static electricity nor electrical overstress is applied to the IC (measures to prevent anti-static, leaks, etc.).
- When incorporating into a set, adopt a set design that does not apply voltage directly to the island section.

## **Package Dimensions**

QON24-P-0505-0.50 Unit: mm



- Note 1) The solder plating portion in four corners of the package shall not be treated as an external terminal.
- Note 2) Don't carry out soldering to four corners of the package.
- Note 3) area: Resin surface

Weight: 0.05 g (typ.)

#### **RESTRICTIONS ON PRODUCT USE**

Handbook" etc..

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